

O P P 2 Q R S T U V W X

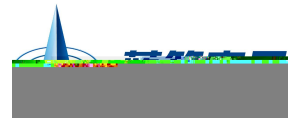
silicon PNP transistor in a SOT-363 Plastic Package.

$Y_{FE} Z [\quad_{CE(sat)} X C D \setminus] X$

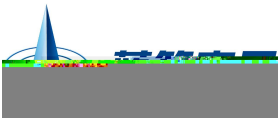
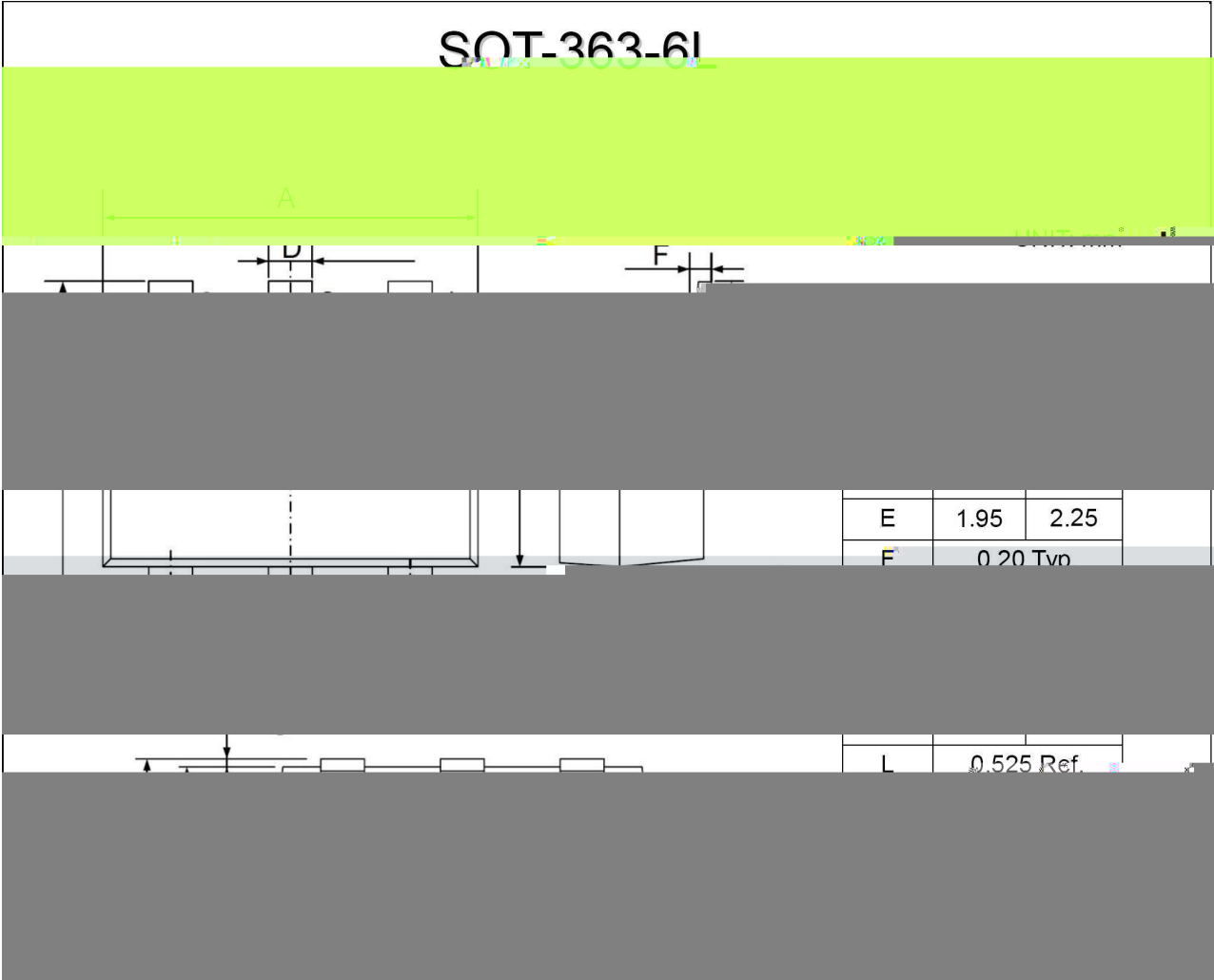
High DC Current Gain, Low Collector to Emitter Saturation Voltage. HF Product.

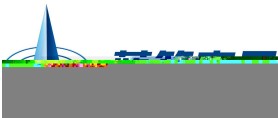
$\wedge _ \backslash a b c) d e X$

General purpose amplifier and switching.

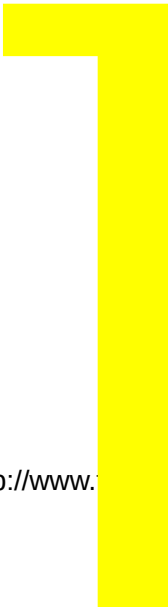
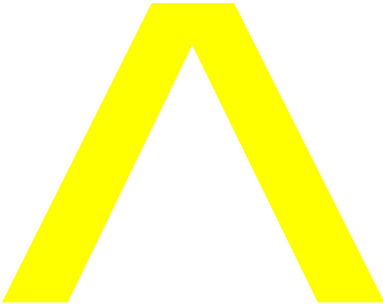
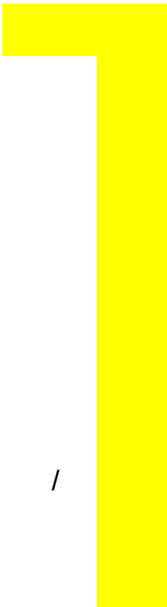


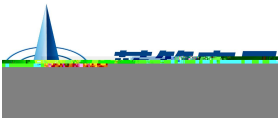
g h Parameter	i j Symbol	h k Rating	l m Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-200	mA





v w f
● f x y 1 z {
A2 f x u j | '
***: x } \ ~ j | ' Z } \ ~ j i ¢





Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- 1

150 180

60 90sec;

1.Preheating:150~180 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5℃

Time:10±1 sec

/ REEL

Package Type

Units 包装数量

封装形式